BTA204S series D, E and F

GENERAL DESCRIPTION

Passivated guaranteed commutation triacs in a plastic envelope suitable for surface mounting, intended for use in motor control circuits or with other highly inductive loads. These devices balance the requirements of commutation performance and gate sensitivity. The "logic level" D series is intended for interfacing with low power drivers, including micro controllers.

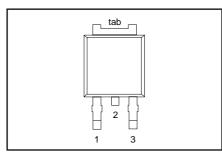
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
	BTA204S - BTA204S - BTA204S -	600D 600E 600F	
V_{DRM}	Repetitive peak off-state voltages	600	V
I _{T(RMS)} I _{TSM}	RMS on-state current Non-repetitive peak on-state current	4 25	A A

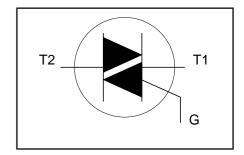
PINNING - SOT428

PIN	DESCRIPTION
1	MT1
2	MT2
3	gate
tab	MT2

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DRM}	Repetitive peak off-state voltages		-	600 ¹	V
I _{T(RMS)} I _{TSM}	RMS on-state current Non-repetitive peak on-state current	full sine wave; $T_{mb} \le 107 ^{\circ}\text{C}$ full sine wave; $T_{j} = 25 ^{\circ}\text{C}$ prior to surge $t = 20 \text{ms}$	-	4	А
		t = 16.7 ms	-	25 27	A
l ² t	I ² t for fusing	t = 10 ms	-	3.1	A A A²s
dl _⊤ /dt	Repetitive rate of rise of on-state current after	$I_{TM} = 6 \text{ A}; I_G = 0.2 \text{ A}; \\ dI_G/dt = 0.2 \text{ A}/\mu\text{s}$		100	A/μs
I _{GM} P _{GM}	triggering Peak gate current Peak gate power		- -	2 5	A W
${f P}_{G(AV)} \ {f T}_{stg} \ {f T}_{j}$	Average gate power Storage temperature Operating junction temperature	over any 20 ms period	-40 -	0.5 150 125	Ç Ç

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¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 $A/\mu s$.

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{\text{th j-mb}}$ $R_{\text{th j-a}}$	Thermal resistance junction to mounting base Thermal resistance junction to ambient	full cycle half cycle pcb (FR4) mounted; footprint as in Fig.14	1 1 1	- - 75	3.0 3.7 -	K/W K/W K/W

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.		MAX.		UNIT
		BTA204S			D	E	F	
I _{GT}	Gate trigger current ²	V _D = 12 V; I _T = 0.1 A T2+ G+ T2+ G-	- -	- -	5 5 5	10 10	25 25	mA mA
I _L	Latching current Holding current	T2- G- $V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$ T2+ G+ T2+ G- T2- G- $V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	- - -		5 6966	10 12 18 12 12	25 20 30 20 20	mA mA mA mA mA
V_{T}	On-state voltage Gate trigger voltage	$I_T = 5 \text{ A}$ $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	- -	1.4 0.7		1.7 1.5		V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A};$	0.25	0.4		-		V
I _D	Off-state leakage current	$T_{j} = 125 ^{\circ}\text{C}$ $V_{D} = V_{DRM(max)}; T_{j} = 125 ^{\circ}\text{C}$	-	0.1		0.5		mA

DYNAMIC CHARACTERISTICS

 $T_j = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.		TYP.	MAX.	UNIT
		BTA204S	D	Е	F			
dV _D /dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)};$ $T_j = 125 °C;$ exponential waveform; gate open circuit	20	30	50	-	-	V/μs
dI _{com} /dt	Critical rate of change of commutating current	$V_{DM} = 400 \text{ V}; T_j = 125 \text{ °C};$ $I_{T_{(RMS)}} = 4 \text{ A};$ $dV_{com}/dt = 10 \text{ V}/\mu\text{s}; gate}$	1.1	2.1	3.0	-	-	A/ms
dl _{com} /dt	Critical rate of change of commutating current	open circuit $V_{DM} = 400 \text{ V}; T_j = 125 ^{\circ}\text{C};$ $I_{T(RMS)} = 4 \text{ A};$ $dV_{com}/dt = 0.1 \text{V}/\mu\text{s}; gate}$	4.5	8.0	15	-	-	A/ms
t _{gt}	Gate controlled turn-on time	open circuit $I_{TM} = 12 \text{ A}; V_D = V_{DRM(max)};$ $I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A}/\mu s$	-	-	1	2	-	μs

² Device does not trigger in the T2-, G+ quadrant.

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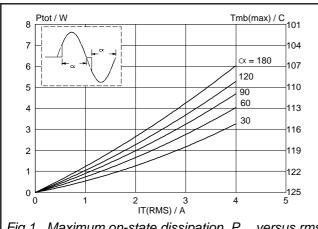


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where $\alpha = conduction$ angle.

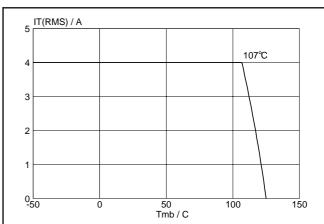


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .

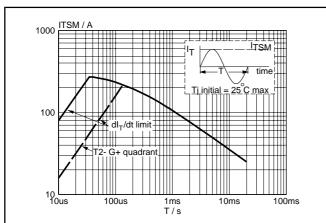


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 20$ ms.

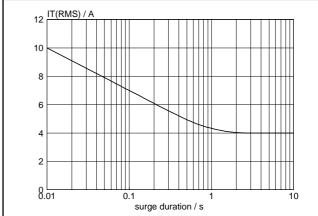


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{mb} \le 107$ °C.

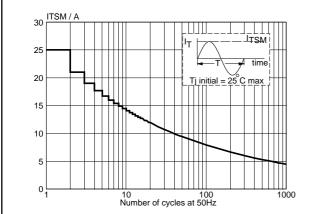


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

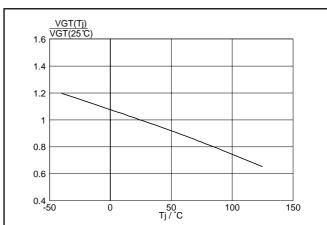
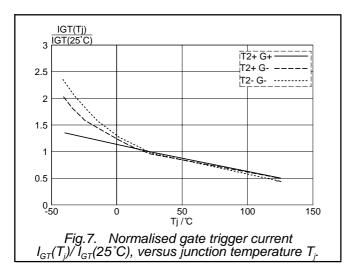
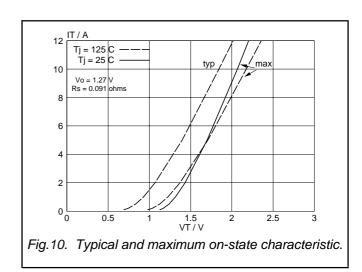
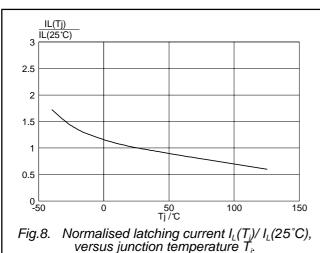


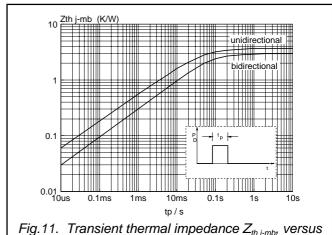
Fig.6. Normalised gate trigger voltage $V_{GT}(T_i)/V_{GT}(25^{\circ}C)$, versus junction temperature T_i .

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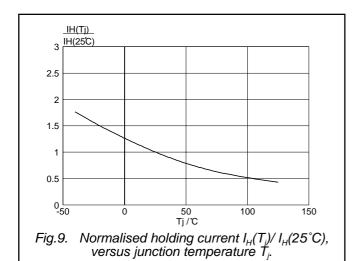
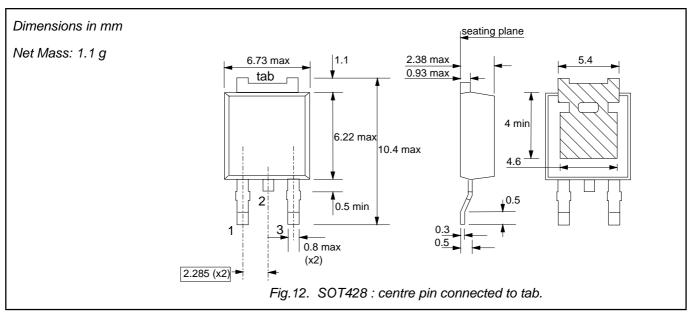


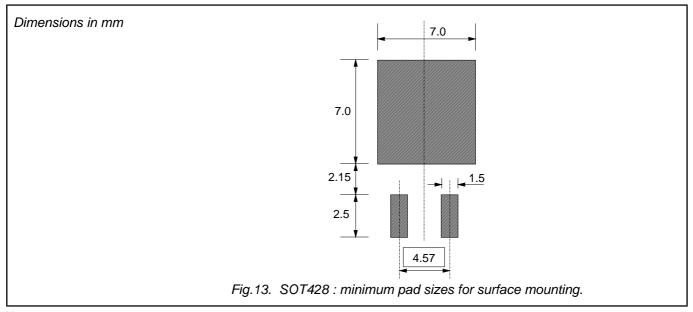
Fig.11. Transient thermal impedance $Z_{th j-mb}$, versus pulse width t_p .

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MECHANICAL DATA



MOUNTING INSTRUCTIONS



Notes

1. Plastic meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Three quadrant triacs guaranteed commutation

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DEFINITIONS

DATA SHEET STATUS					
DATA SHEET STATUS ³	PRODUCT STATUS ⁴	DEFINITIONS			
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice			
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product			
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A			

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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³ Please consult the most recently issued datasheet before initiating or completing a design.

⁴ The product status of the device(s) described in this datasheet may have changed since this datasheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.